EAST - [10769116 trench or pillar split-gate flash.wsp: 1]

File View Edit Tools Window Help

S31: (728346) (select$4 side control) adj (gate line) SG
S32: (985282) (sidewall side adj (wall surface))
S33: (971007) trench pillar column
S34: (9643) S31 near9 S33
S35: (217) S34 near4 S32
S36: (323) S34 with S32
S37: (181) S36 same S30
S38: (40) S37 and S29
S39: (631000) (select$4 side) adj (gate line) SG
S40: (6507) S39 near9 S33
S41: (102) S40 with S32
S42: (20) S41 same S30
S43: (4) S42 and S29
S45: (9) S44 and S29
S46: (9) S45 and S39
S47: (0) Forward citation search 1
S48: (2) Backward citation search 1
S49: (23) Forward citation search 2
S50: (2) S48 and S39
S44: (40) S41 and S30
Favorites
Tagged (3)
UDC
Queue
Trash

New Search | Browse | Search | Clear

DBs: US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

Default operator: OR

Plurals

Highlight all hit terms initially

S41 and S30

Nov 2004

BRS form | IS&R form | Image | Text | HTML

	U	T	Inventor	Document I	Issue	P	Title	Current	Current XR	Retrieval	S	C	P					Image Doc	P
1			Fan, Der-Tsyr	US 2004013	20040	3	Flash memory with trench select gate and fa	365/185	365/51									US 200401	
2			Sakui; Koji et	US 6577533	20030	5	Nonvolatile semiconductor memory and meth	365/185	257/317; 2									US 657753	
3			Prall; Kirk	US 6759707	20040	2	2F2 memory device system	257/315	257/314									US 675970	
4			Harari, Eliyah	US 2004021	20041	1	Non-volatile memory cells utilizing substrate	257/315										US 200402	
5			Chang; Ko-Hs	US 2004018	20041	1	SPLIT GATE FLASH MEMORY CELL AND M	438/266										US 200401	
6			Hsu; Cheng-Y	US 2004018	20040	1	Flash memory device with selective gate wit	257/316										US 200401	
7			Prall, Kirk	US 2004014	20040	2	2F2 memory device	365/145	257/E21.68									US 200401	
8			Yamauchi, Yo	US 2004010	20040	1	Nonvolatile semiconductor memory and meth	365/185										US 200401	
9			Chen, Chiou-F	US 2004005	20040	4	Self-aligned split-gate NAND flash memory a	365/185										US 200400	
10			Harari, Eliyah	US 2004000	20040	2	Non-volatile memory cells utilizing substrate	257/315	257/316;									US 200400	

Hits | Details | HTML

Ready

NUM